

ABSTRACT OF THE DISCLOSURE

There is provided an active matrix type display device in which the display device is formed of a driver circuit with an insulated gate FET capable of operating at high speed, and even if an area of a pixel electrode per unit pixel is made small, sufficient storage capacitance can be obtained. In a semiconductor device comprising an active matrix circuit with an insulated gate field effect transistor having at least an active layer made of single crystalline semiconductor, an organic resin insulating layer is formed over the insulated gate field effect transistor, a storage capacitance is formed of a light shielding layer formed over the organic resin insulating layer, a dielectric layer formed to be in close contact with the light shielding layer, and a light reflecting electrode connected to the insulated gate field effect transistor.